

Agne Johannessen

List of Publications by Year in descending order

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docs citations

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times ranked

222
citing authors

#	ARTICLE	IF	CITATIONS
1	Signal Amplification of a Gravimetric Glucose Biosensor Based on the Concanavalin Aâ€“Dextran Affinity Assay. IEEE Sensors Journal, 2021, 21, 4391-4404.	4.7	3
2	The Characterisation and Quantification of Immobilised Concanavalin A on Quartz Surfaces Based on The Competitive Binding to Glucose and Fluorescent Labelled Dextran. Applied Sciences (Switzerland), 2019, 9, 318.	2.5	8
3	The impact of area on BAW resonator performance and an approach to device miniaturization. Ultrasonics, 2019, 94, 92-101.	3.9	10
4	A Design Approach for High-Q FBARs With a Dual-Step Frame. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2018, 65, 1717-1725.	3.0	17
5	Design of a Love wave mode device for use in a microfabricated glucose sensor. , 2016, , .		2
6	Improvement of methods in analyzing the propagation of plate waves in FBARs. , 2016, , .		1
7	Peculiarities of photoluminescence of vertical n+/n-GaAs/Al _{0.25} Ga _{0.75} As MBE- and MOCVD-grown structures designed for microwave detectors. Applied Physics A: Materials Science and Processing, 2015, 120, 1133-1140.	2.3	1
8	The Increase of Radiative Lifetime of Free Excitons in Selectively Si-doped GaAs/Al _x Ga _{1-x} As Heterostructures. Medziagotyra, 2014, 20, .	0.2	0
9	Design of high-Q Thin Film Bulk Acoustic resonator using dual-mode reflection. , 2014, , .		10
10	Dynamic photoluminescence studies of vertical n+/n-GaAs/Al _{0.2} Ga _{0.8} As structures designed for microwave electronics. Physica Scripta, 2013, 87, 065701.	2.5	0
11	Photoluminescence lifetimes in GaAs/Al _{0.3} Ga _{0.7} As structures designed for microwave and terahertz detectors. Lithuanian Journal of Physics, 2013, 53, 119-126.	0.4	0
12	Light emission lifetimes in p-type Î-doped GaAs/AlAs multiple quantum wells near the Mott transition. Journal of Applied Physics, 2012, 112, 043105.	2.5	5
13	Enhanced light emission in nanostructures. Lithuanian Journal of Physics, 2011, 51, 292-302.	0.4	4
14	Photoluminescence characterisation of GaAs/AlGaAs structures designed for microwave and terahertz detectors. Lithuanian Journal of Physics, 2011, 51, 330-334.	0.4	6
15	Enhanced exciton photoluminescence in the selectively Si-doped GaAs/Al _x Ga _{1-x} As heterostructures. Journal of Applied Physics, 2010, 108, 063522.	2.5	9
16	Impurity-related photoluminescence line shape asymmetry in GaAs/AlAs multiple quantum wells: Fractional-dimensional space approach. Journal of Applied Physics, 2010, 107, .	2.5	11
17	<title>Phonon sidebands in photoluminescence of beryllium Î-doped GaAs/AlAs multiple quantum wells</title>. , 2006, , .		0
18	Behaviour of optical transitions in GaAs/AlAs with highly Be Î-doped MQWs. Lithuanian Journal of Physics, 2005, 45, 201-206.	0.4	5

#	ARTICLE	IF	CITATIONS
19	Dependence of anisotropy and damping on shape and aspect ratio in micron sized Ni ₈₁ Fe ₁₉ elements. Journal of Applied Physics, 2004, 95, 6998-7000.	2.5	12
20	Shape-dependent anisotropy and damping of picosecond magnetisation dynamics in a micron sized Ni ₈₁ Fe ₁₉ element. Journal of Magnetism and Magnetic Materials, 2004, 272-276, 2121-2122.	2.3	6
21	Imaging the dephasing of spin wave modes in a square thin film magnetic element. Physical Review B, 2004, 69, .	3.2	59
22	Observation of incoherent picosecond magnetisation dynamics in micron sized Ni ₈₁ Fe ₁₉ elements by time resolved scanning Kerr effect microscopy. IET Science, Measurement and Technology, 2003, 150, 260-263.	0.7	8
23	Anisotropy, damping, and coherence of magnetization dynamics in a 10 ¹ / ₄ m square Ni ₈₁ Fe ₁₉ element. Applied Physics Letters, 2003, 82, 3065-3067.	3.3	52
24	Lorentz microscopy analysis of arrays of rhombic elements. IEEE Transactions on Magnetics, 2003, 39, 2672-2674.	2.1	2
25	Interactions in magnetic arrays for storage and computation. Microelectronic Engineering, 2001, 57-58, 975-979.	2.4	6
26	Excitonic photoluminescence quenching by impact ionization of excitons and donors in GaAs/Al _{0.35} Ga _{0.65} As quantum wells with an in-plane electric field. Physical Review B, 2000, 62, 15871-15878.	3.2	2
27	Influence of Electric Field on Photoluminescence Quenching in GaAs/AlGaAs Quantum Wells. Materials Science Forum, 1999, 297-298, 253-256.	0.3	0